

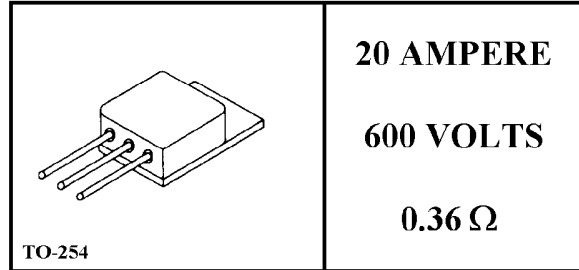


NES
NEW ENGLAND SEMICONDUCTOR

NSF206036

POWER MOSFET N CHANNEL

- REPETITIVE AVALANCHE RATINGS
- LOW $R_{DS(ON)}$
- LOW DRIVE REQUIREMENT
- DYNAMIC dv/dt RATING



20 AMPERE

600 VOLTS

0.36 Ω

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

PARAMETERS / TEST CONDITIONS		SYMBOL	VALUE	UNITS
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	20	A
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	150	W
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Lead Temperature (1/16" from case for 10 secs.)		T_L	300	$^\circ\text{C}$

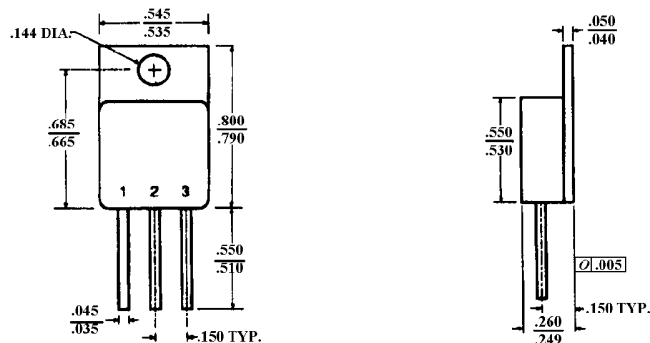
THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYP.	MAX.	UNITS
Junction-to-Case	$R_{\theta JC}$		0.83	K/W

(1) Pulse width limited by maximum junction temperature.

MECHANICAL OUTLINE

PIN 1: DRAIN
PIN 2: SOURCE
PIN 3: GATE



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T4-4.8-860-936 REV: --



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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

PARAMETERS / TEST CONDITIONS		SYMBOL	MIN.	TYP.	MAX.	UNITS
Drain-Source Breakdown Voltage $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$		$V_{(BR)DSS}$	600			V
Gate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$		$V_{GS(th)}$	2.0		4.5	V
Gate-Body Leakage $V_{GS} = \text{At Rated } V_{GS}$		I_{GSS}			± 100	nA
Zero Gate Voltage Drain Current $V_{DS} = \text{max Rating}, V_{GS} = 0\text{ V}$		I_{DSS}			200	μA
Zero Gate Voltage Drain Current $V_{DS} = 80\% \text{ max } V_{(BR)DSS}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$		I_{DSS}			1000	μA
Drain-Source On-State Resistance (2) $V_{GS} = 0\text{ V}, I_D = 50\% \text{ Rated } I_D$		$r_{DS(on)}$			0.36	Ω
Input Capacitance	$V_{GS} = 0\text{ V}$	C_{iss}			4500	pF
Output Capacitance	$V_{DS} = 25\text{ V}$	C_{oss}			420	
Reverse Transfer Capacitance	$f = 1.0\text{ MHz}$	C_{rss}			140	
Total Gate Charge	$V_{DS} = V_{(BR)DSS}$ $V_{GS} = 10\text{ V}, I_D = 10\text{ A}$ (Gate charge is essentially independent of operating temperature.)	Q_g			170	nC
Gate-Source Charge		Q_{gs}			40	
Gate -Drain Charge		Q_{gd}			85	
Turn-On Delay Time	$V_{dd} = 50\% V_{DS},$ $I_D = 10\ \text{A},$ $R_G = 6.2\ \Omega$ (Switching time is essentially independent of operating temperature.)	$t_{d(on)}$			40	ns
Rise Time		t_r			60	
Turn-Off Delay Time		$t_{d(off)}$			150	
Fall Time		t_f			60	

SOURCE-DRAIN DIODE RATINGS & CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

PARAMETERS / TEST CONDITIONS		SYMBOL	MIN.	TYP.	MAX.	UNITS
Forward Voltage (2) $I_F = I_S, V_{GS} = 0\text{ V}$		V_{SD}			1.5	V
Reverse Recovery Time $I_F = 10\text{ A}, dI/dt = 100\text{ A}/\mu\text{S}$		t_{rr}			800	ns

(1) Pulsed width limited by maximum junction temperature.

(2) Pulse Test: Pulse width < 300 μsec . Duty cycle $\leq 2\%$.

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